

PC713VxNSZXF Series

DIP 6 pin Includes Base Terminal Connection Photocoupler



■ Description

PC713VxNSZXF Series contains an IRED optically coupled to a phototransistor.

It is packaged in a 6 pin DIP, available in SMT gullwing lead-form option.

Input-output isolation voltage(rms) is 5.0kV.

Collector-emitter voltage is 80V and CTR is 50% to 600% at input current of 5mA.

■ Features

- 1. 6 pin DIP package
- Double transfer mold package (Ideal for Flow Soldering)
- 3. With base terminal
- 4. High collector-emitter voltage (V_{CEO}:80V)
- 5. High isolation voltage between input and output (V_{iso(rms)}: 5.0kV)
- 6. Lead-free and RoHS directive compliant

■ Agency approvals/Compliance

- Recognized by UL1577 (Double protection isolation), file No. E64380 (as model No. PC713V)
- 2. Approved by VDE, DIN EN60747-5-2^(*) (as an option), file No. 40008189 (as model No. **PC713V**)
- 3. Package resin: UL flammability grade (94V-0)

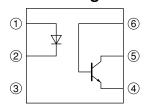
■ Applications

- 1. Home appliances
- 2. Programmable controllers
- 3. Personal computer peripherals

^(*) DIN EN60747-5-2: successor standard of DIN VDE0884



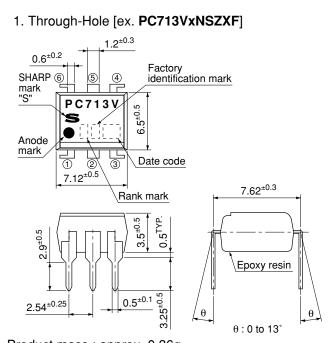
■ Internal Connection Diagram



- 1 Anode
- ② Cathode
- ③ NC
- 4 Emitter
- ⑤ Collector
- 6 Base

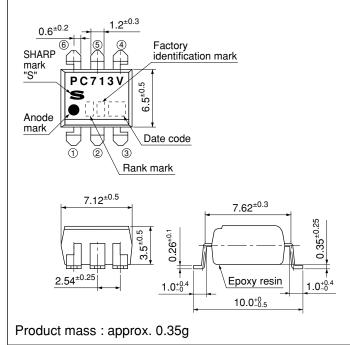
■ Outline Dimensions

(Unit: mm)

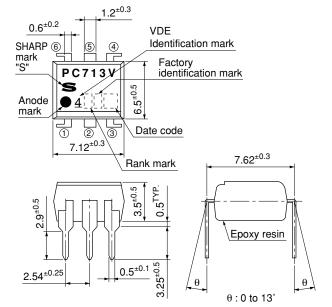


Product mass: approx. 0.36g

3. SMT Gullwing Lead-Form [ex. PC713VxNIPXF]

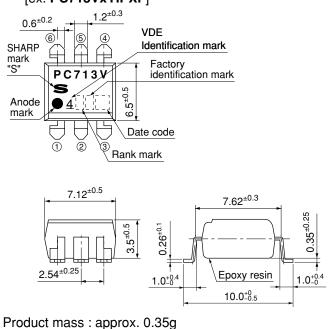


2. Through-Hole (VDE option) [ex. PC713VxYSZXF]



Product mass: approx. 0.36g

4. SMT Gullwing Lead-Form (VDE option) [ex. PC713VxYIPXF]



Plating material: SnCu (Cu: TYP. 2%)



Date code (2 digit)

	1st o	digit		2nd digit		
	Year of p	roduction		Month of production		
A.D.	Mark	A.D	Mark	Month	Mark	
1990	A	2002	P	January	1	
1991	В	2003	R	February	2	
1992	С	2004	S	March	3	
1993	D	2005	T	April	4	
1994	Е	2006	U	May	5	
1995	F	2007	V	June	6	
1996	Н	2008	W	July	7	
1997	J	2009	X	August	8	
1998	K	2010	A	September	9	
1999	L	2011	В	October	0	
2000	M	2012	С	November	N	
2001	N	:	:	December	D	

repeats in a 20 year cycle

Factory identification mark

Factory identification Mark	Country of origin	
no mark	I	
	Japan	
	Indonesia	
_	China	

^{*} This factory marking is for identification purpose only.

Please Contact the local SHARP sales reprsentative to see the actual status of the production.

Rank mark
Refer to the Model Line-up



■ Absolute Maximum Ratings

■ Absolute Maximum Ratings $(T_a=25^{\circ}C_a=10^{\circ})$							
	Parameter	Symbol	Rating	Unit			
	Forward current	I_{F}	50	mA			
Input	*1 Peak forward current	I_{FM}	1	A			
Inj	Reverse voltage	V_R	6	V			
	Power dissipation	P	70	mW			
	Collector-emitter voltage	V_{CEO}	80	V			
	Emitter-collector voltage	V_{ECO}	6	V			
Output	Collector-base voltage	V_{CBO}	80	V			
Out	Emitter-base voltage	V_{EBO}	6	V			
	Collector current	I_{C}	50	mA			
	Collector power dissipation	P_{C}	150	mW			
-	Total power dissipation	P _{tot}	170	mW			
	Operating temperature	T_{opr}	-25 to +100	°C			
- 5	Storage temperature	T_{stg}	-40 to +125	°C			
*2 Isolation voltage		V _{iso (rms)}	5	kV			
*3 (Soldering temperature	T_{sol}	260	°C			

^{*1} Pulse widths100µs, Duty ratio: 0.001 *2 40 to 60%RH, AC for 1minute, f=60Hz *3 For 10s

■ Electro-optical Characteristics

 $(T_a=25^{\circ}C)$

		•					
Parameter			Conditions	MIN.	TYP.	MAX.	Unit
Forward voltage		V_F	$I_F=20mA$	_	1.2	1.4	V
Peak forward voltage		V_{FM}	I _{FM} =0.5A	-	_	3.0	V
Reverse current		I_R	$V_R=4V$	_	_	10	μΑ
Terminal capacitance		C_t	V=0, f=1kHz	-	30	250	pF
Collector dark current		I_{CEO}	$V_{CE}=50V, I_{F}=0$	-	_	100	nA
Collector-emitter breakdown voltage		BV _{CEO}	I _C =0.1mA, I _F =0	80	_	_	V
Emitter-base breakdown voltage		$\mathrm{BV}_{\mathrm{EBO}}$	$I_{E}=10\mu A, I_{F}=0$	6	_	_	V
Collector-base breakdown voltage		BV_{CBO}	$I_{C}=0.1 \text{ mA}, I_{F}=0$	80	_	_	V
Current transfer ratio		I_{C}	$I_F=5mA$, $V_{CE}=5V$	2.5	-	30	mA
Collector-emitter saturation voltage		V _{CE (sat)}	$I_F=20\text{mA}, I_C=1\text{mA}$	-	0.1	0.2	V
Isolation resistance		R _{ISO}	DC500V, 40 to 60%RH	5×10 ¹⁰	1×10 ¹¹	-	Ω
Floating capacitance		C_{f}	V=0, f=1MHz	-	0.6	1.0	pF
Cut-off frequency		f_C	$V_{CE}=5V$, $I_{C}=2mA$, $R_{L}=100\Omega$ $-3dB$	-	80	_	kHz
Daamamaa tima	Rise time	t_r	V 2V I 2m A D 1000	_	4	18	μs
Response time	Fall time	t_{f}	$\mathbf{v}_{\text{CE}} = 2 \mathbf{v}, \mathbf{I}_{\text{C}} = 2 \text{IIIA}, \mathbf{K}_{\text{L}} = 100 \Omega$	_	3	18	μs
	Forward volta Peak forward Reverse currer Perminal capa Collector dark Ollector-emitter break Mitter-base breakd Ollector-base breakd Current transfi Ollector-emitter satures Solation resis	Forward voltage Peak forward voltage Reverse current Cerminal capacitance Collector dark current ollector-emitter breakdown voltage mitter-base breakdown voltage collector-base breakdown voltage Current transfer ratio ollector-emitter saturation voltage solation resistance Cloating capacitance Cut-off frequency Rise time	Forward voltage V_F Peak forward voltage V_{FM} Reverse current I_R Cerminal capacitance C_t Collector dark current I_{CEO} Collector-emitter breakdown voltage I_CEO} mitter-base breakdown voltage I_CEO} Current transfer ratio I_CEO} Current transfer ratio I_CEO} collector-emitter saturation voltage I_CEO} Current transfer ratio I_CEO} Collector-emitter saturation voltage I_CEO} Current transfer ratio I_CEO} Collector-emitter saturation voltage I_CEO}	Forward voltage V_F $I_F=20mA$ Peak forward voltage V_{FM} $I_{FM}=0.5A$ Reverse current I_R $V_R=4V$ Cerminal capacitance C_t $V=0, f=1kHz$ Collector dark current I_{CEO} $V_{CE}=50V, I_F=0$ Collector-emitter breakdown voltage $I_C=0.1mA, I_F=0$ mitter-base breakdown voltage $I_C=0.1mA, I_F=0$ Current transfer ratio I_C $I_F=5mA, V_{CE}=5V$ Current transfer ratio I_C $I_F=5mA, V_{CE}=5V$ Current transfer ratio I_C $I_F=20mA, I_C=1mA$ Solution resistance I_{CE} $I_C=0.1mA$ Collector-emitter saturation voltage	Forward voltage V_F $I_F=20mA$ $ I_{FM}=0.5A$ $ I_{FM}=0.$	Forward voltage V_F $I_F=20mA$ $ 1.2$ $I_{FM}=0.5A$ $ 0.2$ $I_{FM}=0.5A$ $ 0.3$ $I_{FM}=0.5A$ $ 0.3$ $I_{FM}=0.5A$ $ 0.3$ $I_{FM}=0.5A$ $ 0.3$ $I_{FM}=0.5A$ $ 0.3$ $I_{FM}=0.5A$ $ 0.3$ $I_{FM}=0.5A$ $ 0.3$ $I_{FM}=0.5A$ $I_{FM}=0.$	Forward voltage V_F $I_F=20mA$ - 1.2 1.4 Peak forward voltage V_{FM} $I_{FM}=0.5A$ - - 3.0 Reverse current I_R $V_R=4V$ - - 10 Germinal capacitance C_t $V=0$, $f=1kHz$ - 30 250 Collector dark current I_{CEO} $V_{CE}=50V$, $I_F=0$ - - 100 Collector dark current I_{CEO} $V_{CE}=50V$, $I_F=0$ - - 100 Collector dark current I_{CEO} $V_{CE}=50V$, $I_F=0$ - - 100 Collector-emitter breakdown voltage BV_{CEO} $I_{C}=0.1mA$, $I_F=0$ 80 - - Current transfer ratio I_C $I_{C}=0.1mA$, $I_{F}=0$ 80 - - Current transfer ratio I_C $I_{F}=5mA$, $V_{CE}=5V$ 2.5 - 30 collector-emitter saturation voltage V_{CE} (sat) $I_{F}=20mA$, $I_{C}=1mA$ - 0.1 0.2 solation resistance



■ Model Line-up

Lead Form	Throu	gh-Hole	SMT Gullwing					I _C [mA]
Doolyooo	Sleeve				Taping		Rank mark	$(I_F=5mA,$
Package		50pcs /	' sleeve		1 000pcs / reel		Rank mark	$V_{CE}=5V$,
DIN EN60747-5-2		Approved		Approved		Approved		$T_a=25$ °C)
	PC713V0NSZXF	PC713V0YSZXF	PC713V0NIZXF	PC713V0YIZXF	PC713V0NIPXF	PC713V0YIPXF	with or without	2.5 to 30.0
	PC713V1NSZXF	PC713V1YSZXF	PC713V1NIZXF	PC713V1YIZXF	PC713V1NIPXF	PC713V1YIPXF	A	4.0 to 8.0
	PC713V2NSZXF	PC713V2YSZXF	PC713V2NIZXF	PC713V2YIZXF	PC713V2NIPXF	PC713V2YIPXF	В	6.5 to 13.0
Model No.	PC713V3NSZXF	PC713V3YSZXF	PC713V3NIZXF	PC713V3YIZXF	PC713V3NIPXF	PC713V3YIPXF	С	10.0 to 20.0
	PC713V5NSZXF	PC713V5YSZXF	PC713V5NIZXF	PC713V5YIZXF	PC713V5NIPXF	PC713V5YIPXF	A or B	4.0 to 13.0
	PC713V6NSZXF	PC713V6YSZXF	PC713V6NIZXF	PC713V6YIZXF	PC713V6NIPXF	PC713V6YIPXF	B or C	6.5 to 20.0
	PC713V8NSZXF	PC713V8YSZXF	PC713V8NIZXF	PC713V8YIZXF	PC713V8NIPXF	PC713V8YIPXF	A, B or C	4.0 to 20.0

Please contact a local SHARP sales representative to inquire about production status.



Fig.1 Forward Current vs. Ambient Temperature

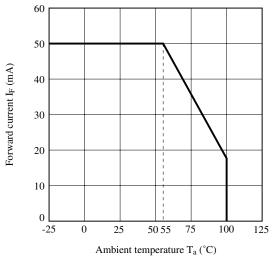


Fig.3 Collector Power Dissipation vs. Ambient Temperature

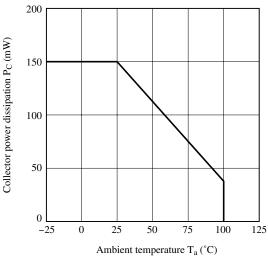


Fig.5 Peak Forward Current vs. Duty Ratio

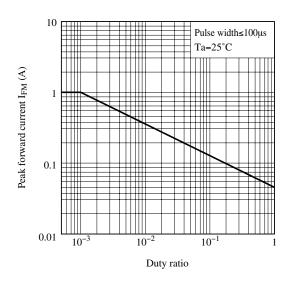


Fig.2 Diode Power Dissipation vs. Ambient Temperature

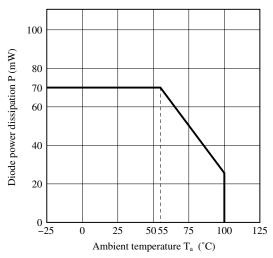


Fig.4 Total Power Dissipation vs. Ambient Temperature

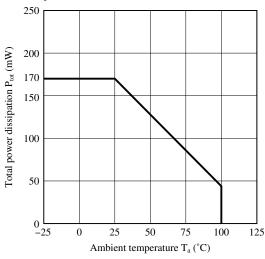


Fig.6 Forward Current vs. Forward Voltage

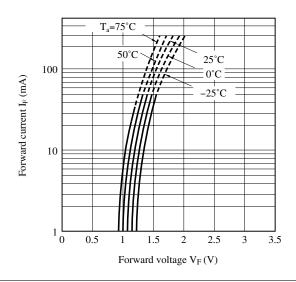




Fig.7 Current Transfer Ratio vs. Forward Current

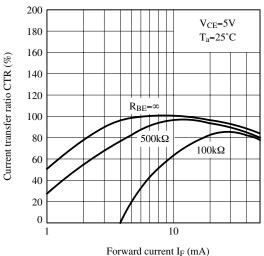


Fig.9 Relative Current Transfer Ratio vs.
Ambient Temperature

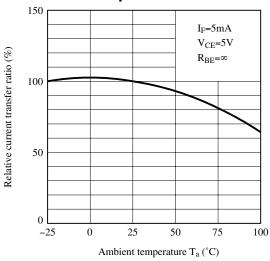


Fig.11 Collector Dark Current vs. Ambient Temperature

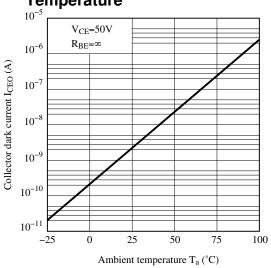


Fig.8 Collector Current vs. Collectoremitter Voltage

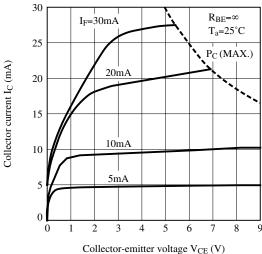


Fig.10 Collector - emitter Saturation Voltage vs. Ambient Temperature

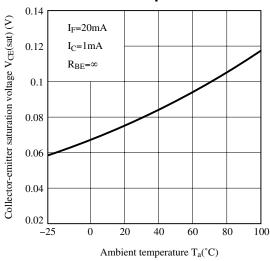


Fig.12 Collector-base Dark Current vs.
Ambient Temperature

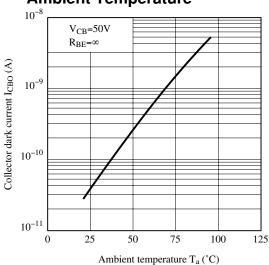




Fig.13 Response Time vs. Load Resistance

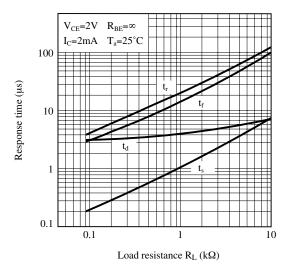


Fig.15 Frequency Response

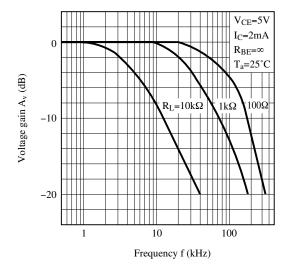
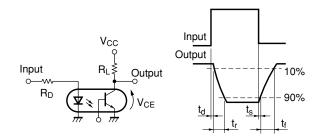
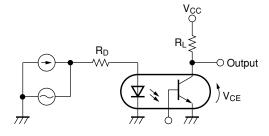


Fig.14 Test Circuit for Response Time



Please refer to the conditions in Fig.13

Fig.16 Test Circuit for Frequency Response



Please refer to the conditions in Fig.15

Remarks: Please be aware that all data in the graph are just for reference and not for guarantee.



■ Design Considerations

Design guide

While operating at I_F<1.0mA, CTR variation may increase.

Please make design considering this fact.

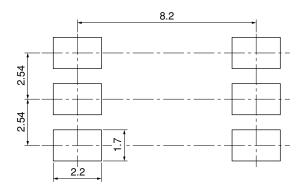
This product is not designed against irradiation and incorporates non-coherent IRED.

Degradation

In general, the emission of the IRED used in photocouplers will degrade over time.

In the case of long term operation, please take the general IRED degradation (50% degradation over 5 years) into the design consideration.

Recommended Foot Print (reference)



(Unit:mm)

[☆] For additional design assistance, please review our corresponding Optoelectronic Application Notes.



■ Manufacturing Guidelines

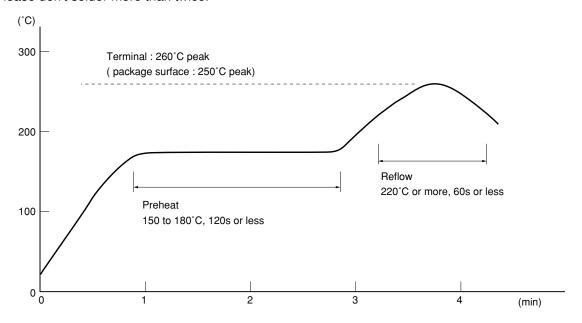
Soldering Method

Reflow Soldering:

Reflow soldering should follow the temperature profile shown below.

Soldering should not exceed the curve of temperature profile and time.

Please don't solder more than twice.



Flow Soldering:

Due to SHARP's double transfer mold construction submersion in flow solder bath is allowed under the below listed guidelines.

Flow soldering should be completed below 270°C and within 10s.

Preheating is within the bounds of 100 to 150°C and 30 to 80s.

Please don't solder more than twice.

Hand soldering

Hand soldering should be completed within 3s when the point of solder iron is below 400°C.

Please don't solder more than twice.

Other notices

Please test the soldering method in actual condition and make sure the soldering works fine, since the impact on the junction between the device and PCB varies depending on the tooling and soldering conditions.



Cleaning instructions

Solvent cleaning:

Solvent temperature should be 45°C or below Immersion time should be 3 minutes or less

Ultrasonic cleaning:

The impact on the device varies depending on the size of the cleaning bath, ultrasonic output, cleaning time, size of PCB and mounting method of the device.

Therefore, please make sure the device withstands the ultrasonic cleaning in actual conditions in advance of mass production.

Recommended solvent materials:

Ethyl alcohol, Methyl alcohol and Isopropyl alcohol

In case the other type of solvent materials are intended to be used, please make sure they work fine in actual using conditions since some materials may erode the packaging resin.

Presence of ODC

This product shall not contain the following materials.

And they are not used in the production process for this product.

Regulation substances: CFCs, Halon, Carbon tetrachloride, 1.1.1-Trichloroethane (Methylchloroform)

Specific brominated flame retardants such as the PBBOs and PBBs are not used in this product at all.

This product shall not contain the following materials banned in the RoHS Directive (2002/95/EC).

•Lead, Mercury, Cadmium, Hexavalent chromium, Polybrominated biphenyls (PBB), Polybrominated diphenyl ethers (PBDE).



■ Package specification

Sleeve package

Package materials

Sleeve: HIPS (with anti-static material)

Stopper: Styrene-Elastomer

Package method

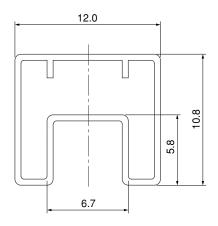
MAX. 50 pcs. of products shall be packaged in a sleeve.

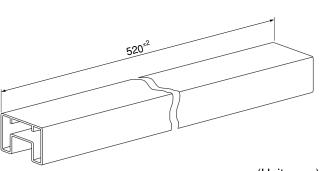
Both ends shall be closed by tabbed and tabless stoppers.

The product shall be arranged in the sleeve with its anode mark on the tabless stopper side.

MAX. 20 sleeves in one case.

Sleeve outline dimensions





(Unit:mm)



● Tape and Reel package

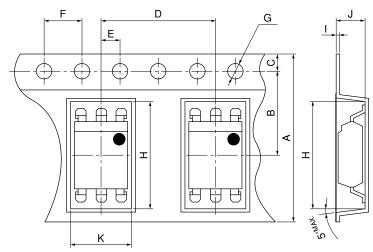
Package materials

Carrier tape: A-PET (with anti-static material)

Cover tape: PET (three layer system)

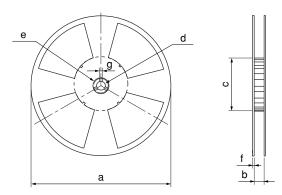
Reel: PS

Carrier tape structure and Dimensions



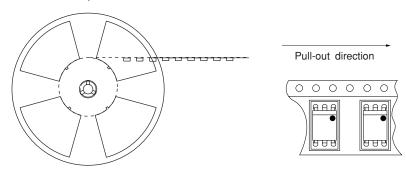
Dimensions List						(Unit:mm)
A	В	C	D	Е	F	G
16.0±0.3	7.5 ^{±0.1}	1.75 ^{±0.1}	12.0 ^{±0.1}	2.0 ^{±0.1}	4.0 ^{±0.1}	φ1.5 + 8.1
Н	I	J	K			
10.4 ^{±0.1}	0.4 ^{±0.05}	4.2 ^{±0.1}	7.8 ^{±0.1}			

Reel structure and Dimensions



Dimensio	ns List	(Unit: mm)		
a	b	c	d	
330	17.5 ^{±1.5}	100±1.0	13 ^{±0.5}	
e	f	g		
23 ^{±1.0}	2.0±0.5	2.0±0.5		

Direction of product insertion



[Packing: 1 000pcs/reel]



■ Important Notices

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 - --- Personal computers
 - --- Office automation equipment
 - --- Telecommunication equipment [terminal]
 - --- Test and measurement equipment
 - --- Industrial control
 - --- Audio visual equipment
 - --- Consumer electronics
- (ii) Measures such as fail-safe function and redundant design should be taken to ensure reliability and safety when SHARP devices are used for or in connection

with equipment that requires higher reliability such as:

- --- Transportation control and safety equipment (i.e., aircraft, trains, automobiles, etc.)
- --- Traffic signals
- --- Gas leakage sensor breakers
- --- Alarm equipment
- --- Various safety devices, etc.
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 - --- Telecommunication equipment [trunk lines]
 - --- Nuclear power control equipment
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[E218] Sheet No.: D2-A04302EN